



# CW1051

## 2~5 Channel Secondary Protection IC

### Features

- 2~5 Cells Application
- Overcharge Protection
  - Threshold from 4.100V to 4.500V
  - 25mV Steps,  $\pm 25\text{mV}$  Accuracy
- Internal Overcharge Protection Delay Time
- Overcharge Delay Counter Reset Time
- Open Wire Protection
- Low Power Dissipation
  - Normal Working  $4\mu\text{A}$  ( $25^\circ\text{C}$ )
- Package Type: MSOP8L, DFN3\*4-8L

### General Description

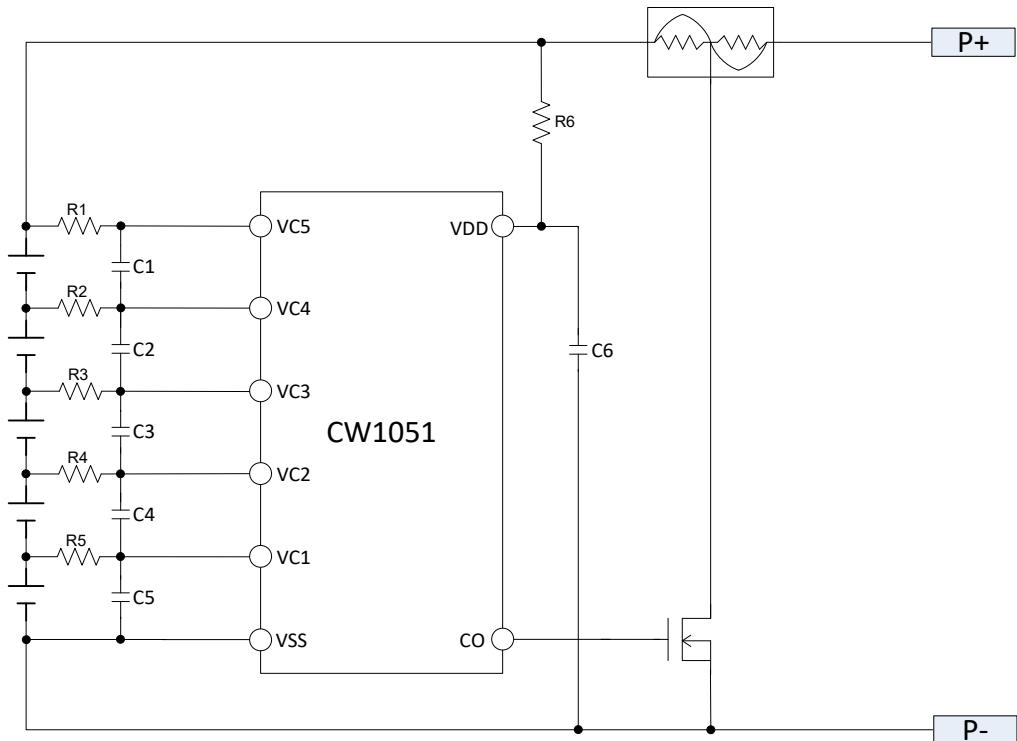
The CW1051 series products are highly integrated secondary protection ICs for 2 to 5 lithium-ion and lithium polymer battery cells connected in series. CW1051 provides overcharge protection for battery pack by measuring each cell's voltage.

### Applications

- NoteBook
- Tablet PC
- E-Tools
- Backup Power Supply
- Other Lithium-ion or Lithium Polymer Battery Packs

## Application Circuits

For 5 cell connect in series (CMOS, Active H)

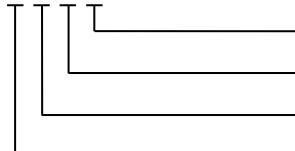


### Recommended parameter

SYMBOL	TYPICAL	RANGE	UNIT
R1,R2,R3,R4,R5	1000	200~2000	Ω
R6	200	200~1000	Ω
C1,C2,C3,C4,C5	0.1	0.1~0.22	μF
C6	0.1	0.1~0.47	μF

**Product Name**

CW1051 X X X X



Package type, D: DFN3\*4-8L M: MSOP8L

Parameter option, from A to Z

Battery type, L: Lithium

Function and revision option, from A to Z

**Ordering Information**

TYPE	OVER CHARGE THRESHOLD [VOC] (V)	HYSTERESIS VOLTAGE <sup>*1</sup> [VHYS] (V)	DELAY TIME <sup>*2</sup> [TOC] (S)	OUTPUT TYPE <sup>*3</sup>		
CW1051ALAM	4.220	0.300	1	CMOS, Active H		
CW1051ALAD						
CW1051ALBM	4.220	0.050	6	CMOS, Active L		
CW1051ALBD						
CW1051ALCM	4.350		1			
CW1051ALCD						
CW1051ALDM	4.400		4	CMOS, Active H		
CW1051ALDD						
CW1051ALEM	4.220		1			
CW1051ALED						
CW1051ALFM	4.300	0.300	1			
CW1051ALFD						
CW1051ALGD	4.300		2	NMOS open drain, Active L		
CW1051ALGM						
CW1051ALHD	4.275	0.050	4			
CW1051ALHM						
CW1051ALJM	4.250	0.100	1	CMOS, Active H		
CW1051ALJD						
CW1051ALKM	4.220		4			
CW1051ALLM	4.250					
CW1051ALMM	4.200					
CW1051ALMD	4.200	0.050	1	CMOS, Active L		
CW1051ALNM	4.175	0.100	4	NMOS open drain Active L		
CW1051ALOM	4.250	0.100	1	CMOS, Active L		
CW1051ALPM	4.175	0.100	1	NMOS open drain Active L		
CW1051ALQD	4.350	0.300	4	CMOS, Active H		
CW1051ALSM	4.200	0.100	1	CMOS, Active H		
CW1051ALRM	4.200	0.100	1	CMOS, Active L		
CW1051ALRD	4.200	0.100	1	CMOS, Active L		
CW1051ALTM	4.325	0.300	6	CMOS, Active H		

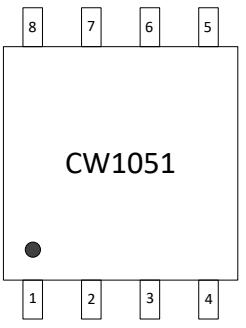
TYPE	OVER CHARGE THRESHOLD [VOC] (V)	HYSERESIS VOLTAGE <sup>*1</sup> [VHYS] (V)	DELAY TIME <sup>*2</sup> [TOC] (S)	OUTPUT TYPE <sup>*3</sup>
CW1051ALUM	3.800	0.100	1	CMOS, Active H
CW1051ALVM	4.250	0.100	1	CMOS, Active L
CW1051ALXM	4.275	0.050	1	CMOS, Active H
CW1051ALXD	4.275	0.050	1	CMOS, Active H
CW1051ALYM	4.220	0.100	6	CMOS, Active H

\*1 Optional hysteresis voltage: 0V, 0.050V, 0.100V, 0.300V

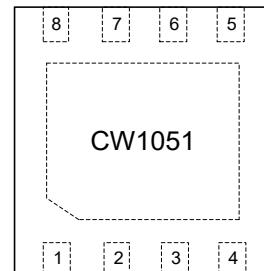
\*2 Optional delay time: 1s, 2s, 4s, 6s

\*3 Optional output type: CMOS active H, CMOS Active L, PMOS open drain Active H, NMOS open drain Active L

## Pin Configuration



MSOP8L Package



DFN3\*4-8L Package

## Pin Descriptions

PIN	NAME	DESCRIPTION
1	VDD	Power supply
2	VC5	Positive input of cell5
3	VC4	Positive input of cell4
4	VC3	Positive input of cell3
5	VC2	Positive input of cell2
6	VC1	Positive input of cell1
7	VSS	Ground
8	CO	Overcharge output driver

## Absolute Maximum Ratings

		VALUE		UNITS
		MIN	MAX	
PIN voltage range respect to VSS	VDD, VCx	-0.3	36	V
PIN voltage range respect CO		-0.3	VDD+0.3	V
Operation Temperature		-40	110	°C
Storage Temperature	T <sub>stg</sub>	-40	125	°C

Caution:

Stresses beyond "Absolute Maximum Ratings" condition may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## ESD Ratings

			MAX	UNITS
V <sub>(ESD)</sub> Rating	Electrostatic discharge	Human body model (HBM) ESD stress voltage	±4000	V
		Charged device model (CDM) ESD stress voltage	±1000	V

## Recommended DC Operating Conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
VDD Input Voltage Range	V <sub>DD</sub>		4.0		28	V
VDD Input Voltage Range	V <sub>DD</sub>	From -40°C to 85°C	4.5		28	
VCx Input Voltage Range	V <sub>Cx</sub>		0		4.5	V

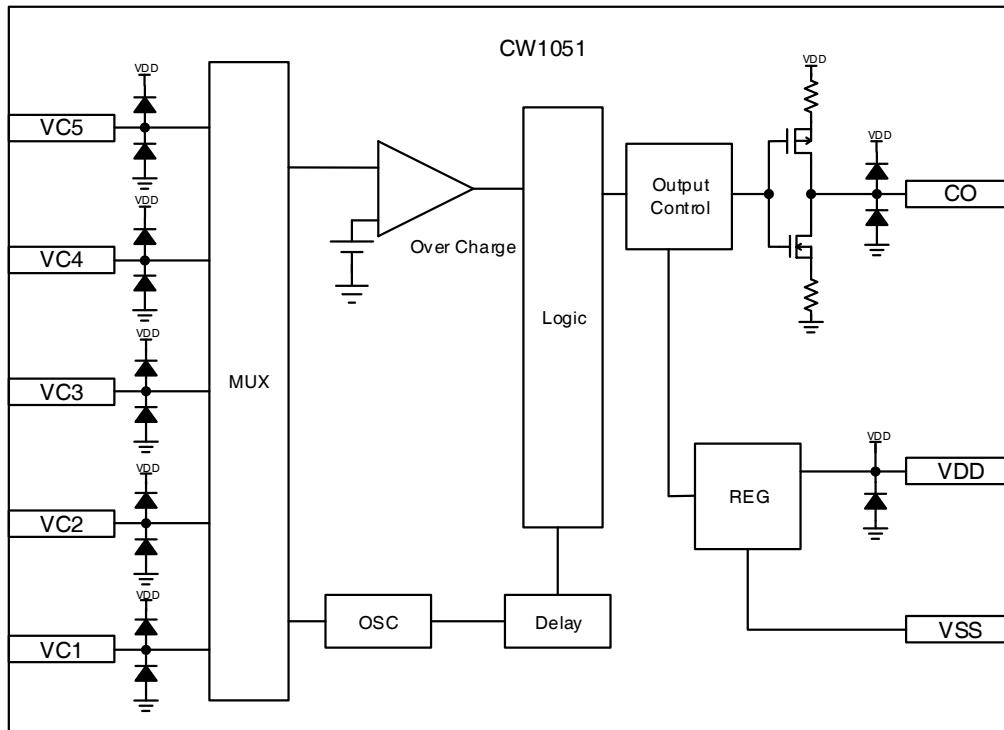
## Electrical Characteristics

Operation under 25°C unless otherwise specified

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
<b>INPUT CURRENT</b>						
Operation Current	I <sub>OPR</sub>	VC1=VC2=VC3=VC4=VC5=3.7V		4	7	µA
<b>VOLTAGE/TEMPERATURE DETECT AND PROTECTION THRESHOLD</b>						
Overcharge Threshold	V <sub>OC</sub>	VC1=VC2=VC3=VC4=3.7V Sweep VC5 from 3.7V to 4.5V	V <sub>OC-</sub> 0.025	V <sub>OC</sub>	V <sub>OC+</sub> 0.025	V
Overcharge Threshold in whole Temperature Range		From -5°C to 55°C	V <sub>OC-</sub> 0.040	V <sub>OC</sub>	V <sub>OC+</sub> 0.040	V
		From -40°C to 110°C	V <sub>OC-</sub> 0.060	V <sub>OC</sub>	V <sub>OC+</sub> 0.060	V
OC Release Threshold V <sub>OCR</sub> =V <sub>OC-</sub> V <sub>HYS</sub>	V <sub>OCR</sub>	VC1=VC2=VC3=VC4=3.7V Sweep VC5 from 4.5V to 3.7V	V <sub>OCR-</sub> 0.025	V <sub>OCR</sub>	V <sub>OCR+</sub> 0.025	V
<b>ACTION DELAY</b>						
Overcharge Delay	t <sub>OC</sub>	VC1=VC2=VC3=VC4=3.7V Sweep VC5 from 3.7V to 4.5V	0.80* t <sub>OC</sub>	t <sub>OC</sub>	1.30* t <sub>OC</sub>	s
Overcharge Release Delay	t <sub>OCR</sub>	VC1=VC2=VC3=VC4=3.7V Sweep VC5 from 4.5V to 3.7V		5		ms
Overcharge Reset Delay	t <sub>RESET</sub>			20		ms
Open-wire Detection Delay	t <sub>OW</sub>	Input capacitor = 0.1µF		2		s
Open-wire Release Delay	t <sub>OWR</sub>			10		ms
<b>PIN OUTPUT VOLTAGE</b>						
CO Logic High Output	V <sub>OC</sub>	VC1=VC2=VC3=VC4=VC5=3.7V	VDD-0.3			V
CO Logic Low Output* <sup>1</sup>		VC1=VC2=VC3=VC4=VC5=4.5V			0.3	V
<b>PIN DRIVE ABILITY</b>						
CO High Output Drive Ability	CO	V <sub>OC</sub> =VDD-0.5V		35		µA
		Source resistance (VDD side)	10	13	16	kΩ
		V <sub>OC</sub> =VSS+0.5V		0.5		mA
		Sink resistance (VSS side)	0.9	1.2	1.5	kΩ

\*1There is several output types, detail please refer to the product selection table. Take CMOS Active H for example here.

## Functional Block Diagram



Notes: Some buffer blocks omitted

## Detailed Description

### Normal State

CW1051 works under a normal state when each cell voltage is less than  $V_{oc}$ .

### Overcharge State

When any cell voltage becomes higher than overcharge threshold voltage ( $V_{oc}$ ) and stays longer than overcharge protection delay time ( $t_{oc}$ ), CO will output a high-level signal, and CW1051 enters over charge state. CO signal can be used to inform the external device or control the MOSFET. If within  $T_{oc}$ , cell voltage drops lower than  $V_{oc}$  but stays shorter than overcharge reset delay time ( $t_{RESET}$ ) before rising up over  $V_{oc}$  again, this spike will be ignored. Otherwise, accumulated delay time of overcharge will be reset. Overcharge protection state will release when all the cell voltages are less than the overcharge release threshold ( $V_{OCR}$ ) and stay longer than the release delay time ( $t_{OCR}$ ).

### Open-wire Detection

Any wire connected between the battery cell and IC will be monitored.

When the wire disconnects and maintains ( $t_{OW}$ ) time, IC will enter to the open-wire protection state.

CO outputs a high-level voltage to cut off the charge loop.

Open-wire protection will release when all wires reconnect and stay longer than the release delay time ( $t_{OWR}$ ).

### Test Mode

Test mode is used to reduce the protection delay time for test of mass production.

CW1051 will enter the test mode when add a  $V_{DD+7V}$  voltage on VDD pin and maintains 80ms. Test mode lasts 8s then recovers to the normal status.

Detailed test mode timing is illustrated as bellow:

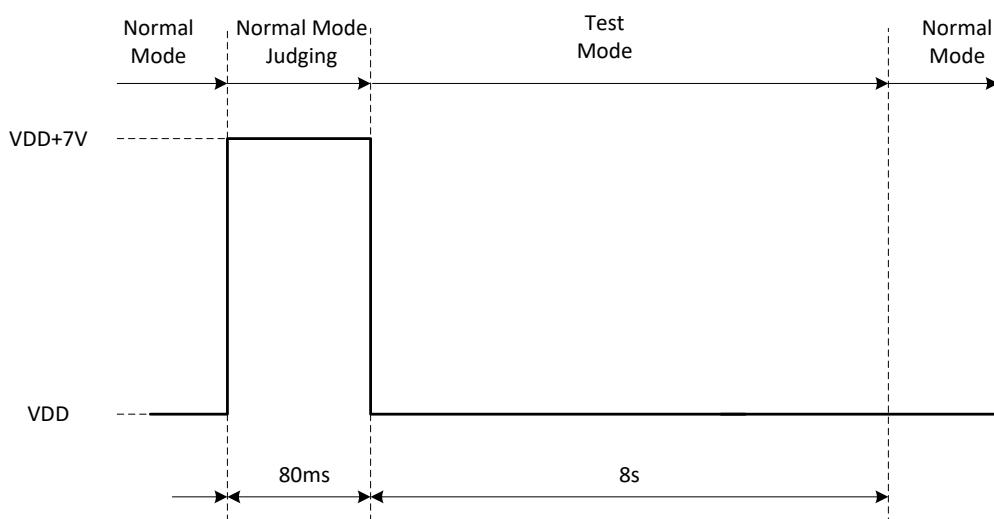
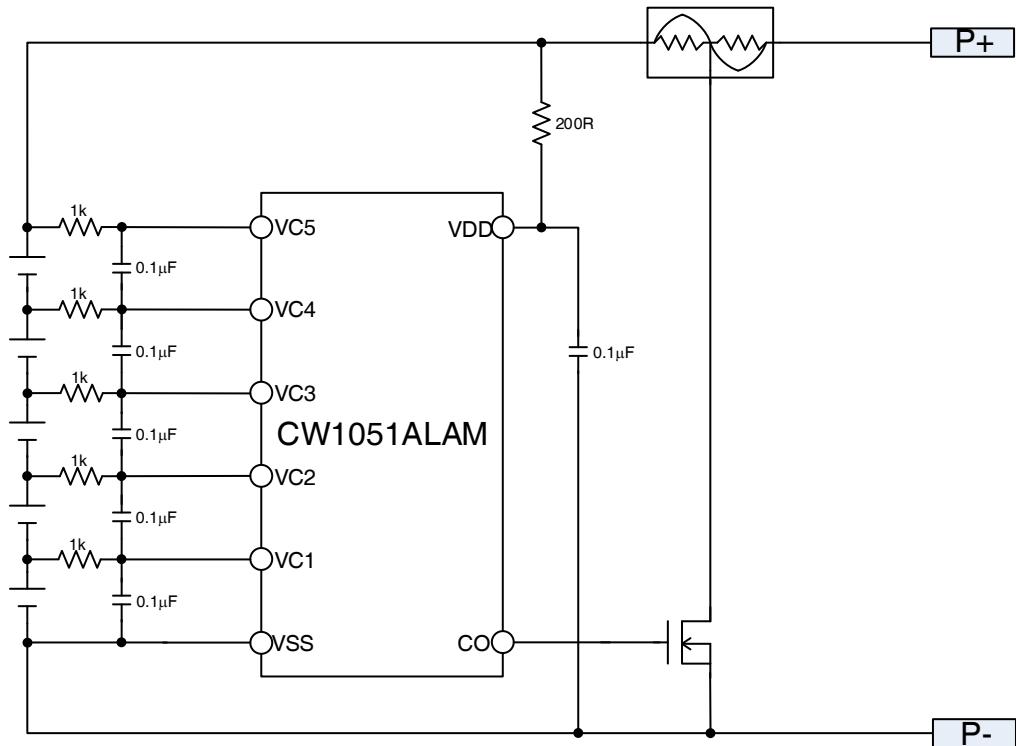
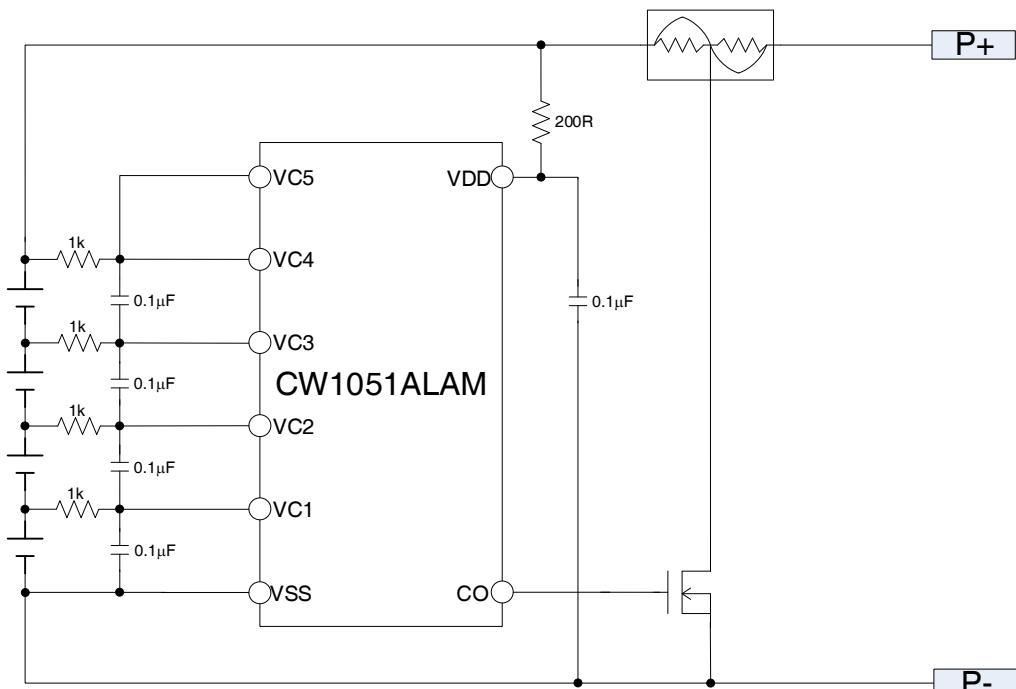


Figure 1. Test Mode Timing

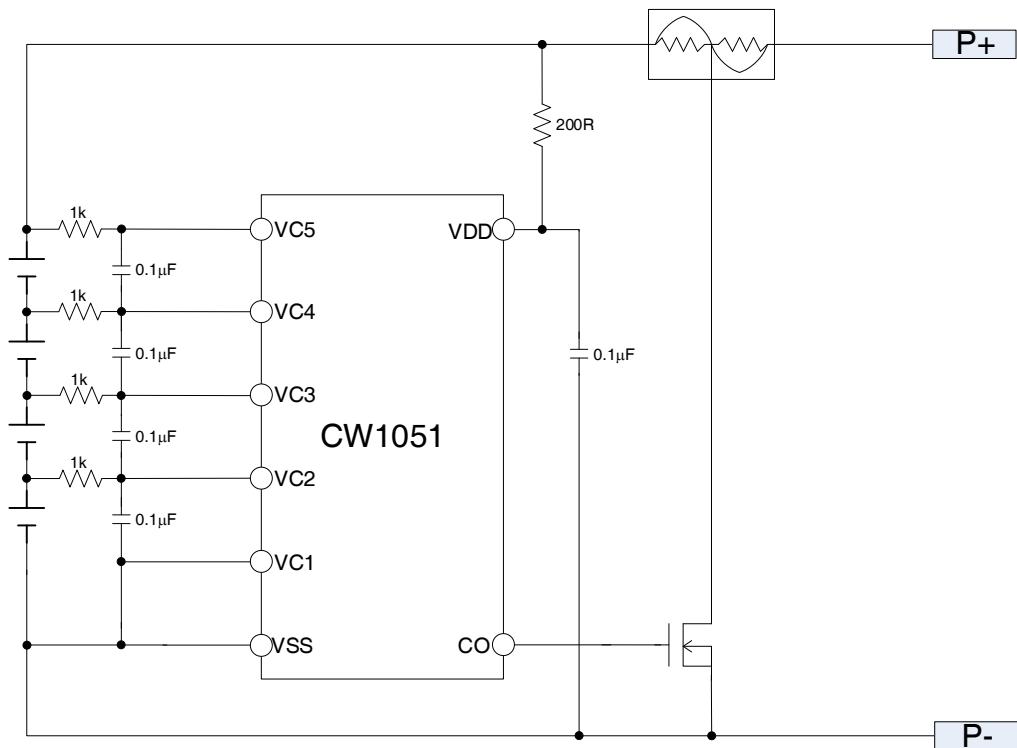
## Reference Schematic



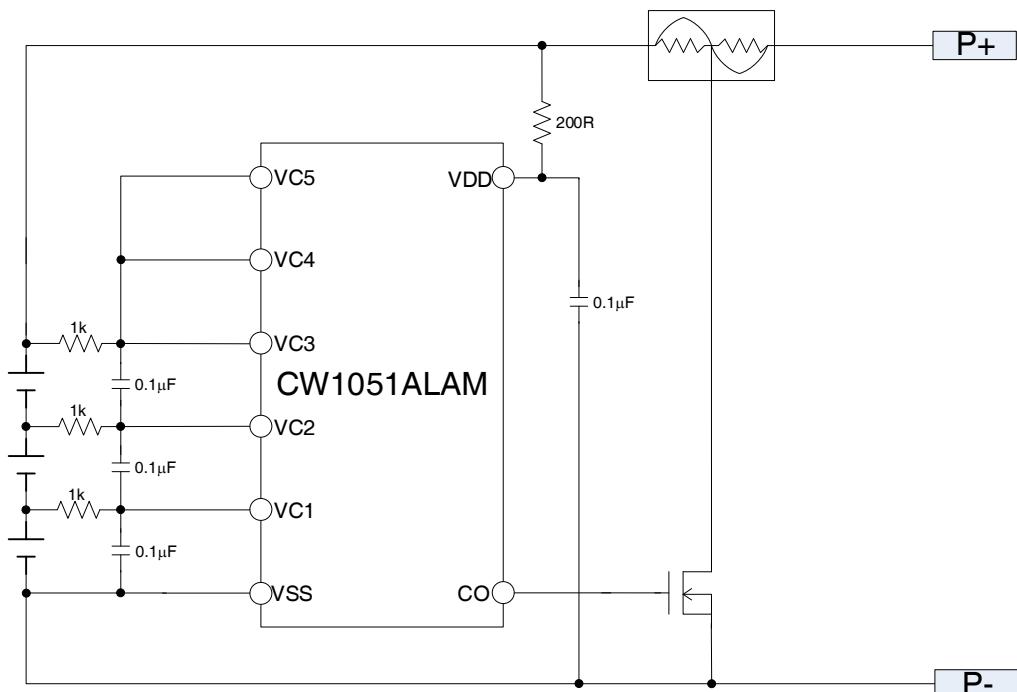
Reference Schematic for 5 cells



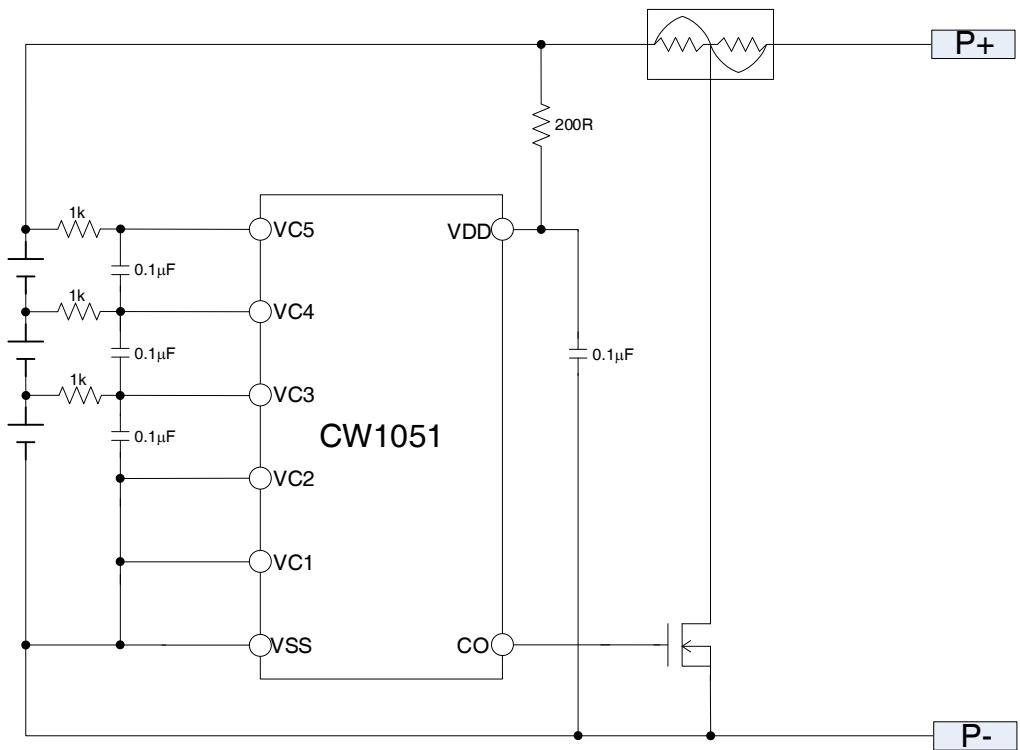
Reference Schematic for 4 cells(connect high side cell)



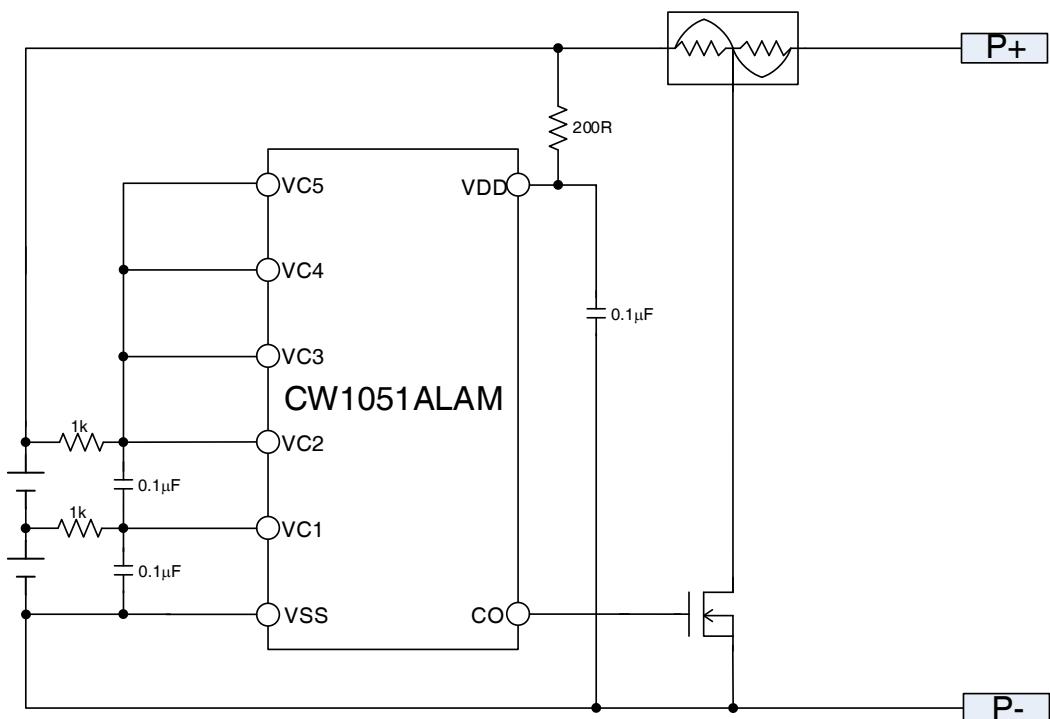
Reference Schematic for 4 cells (connect low side cell)



Reference Schematic for 3 cells(connect high side cell)

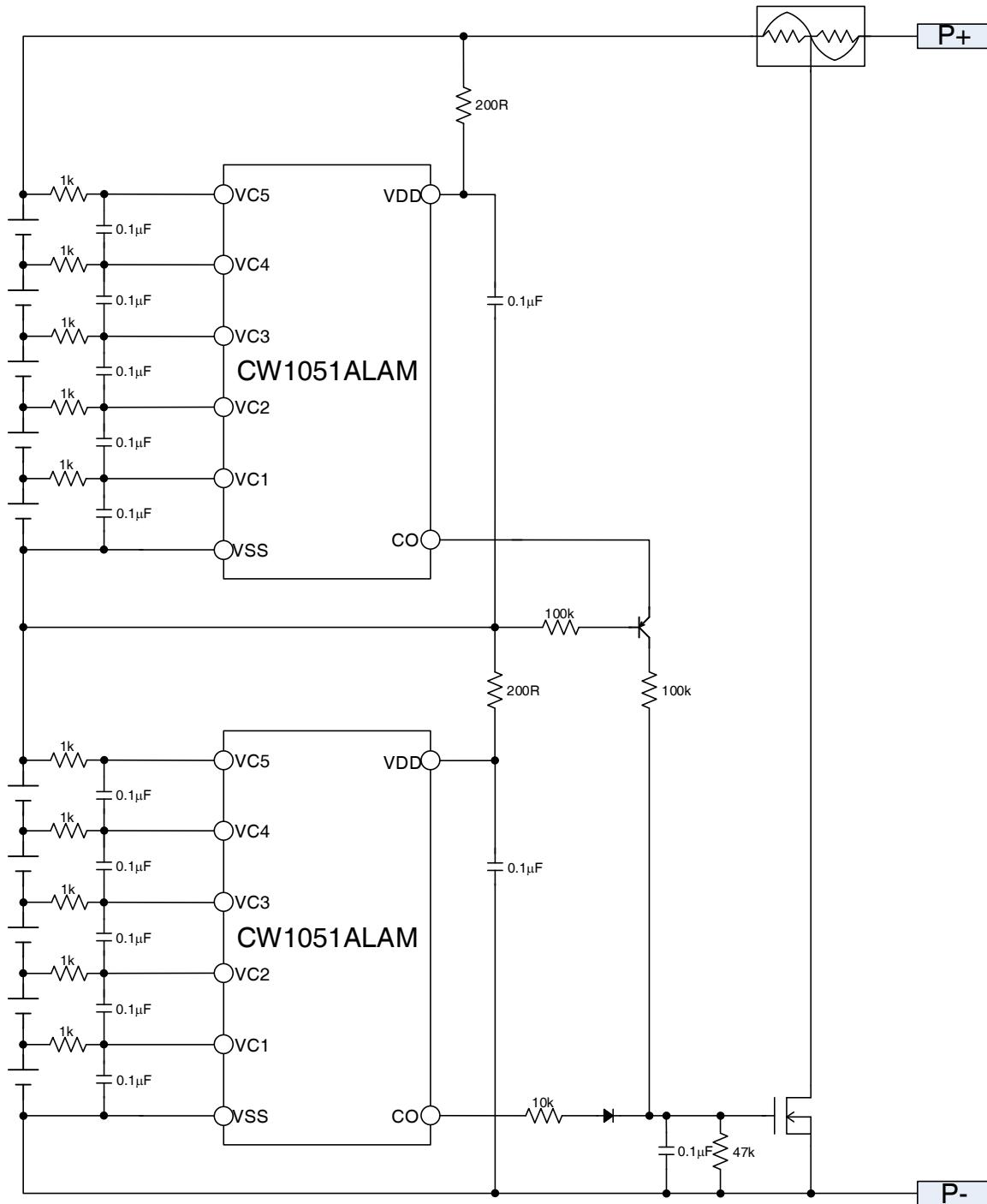


Reference Schematic for 3 cells (connect low side cell)



Reference Schematic for 2 cells(connect high side cell)

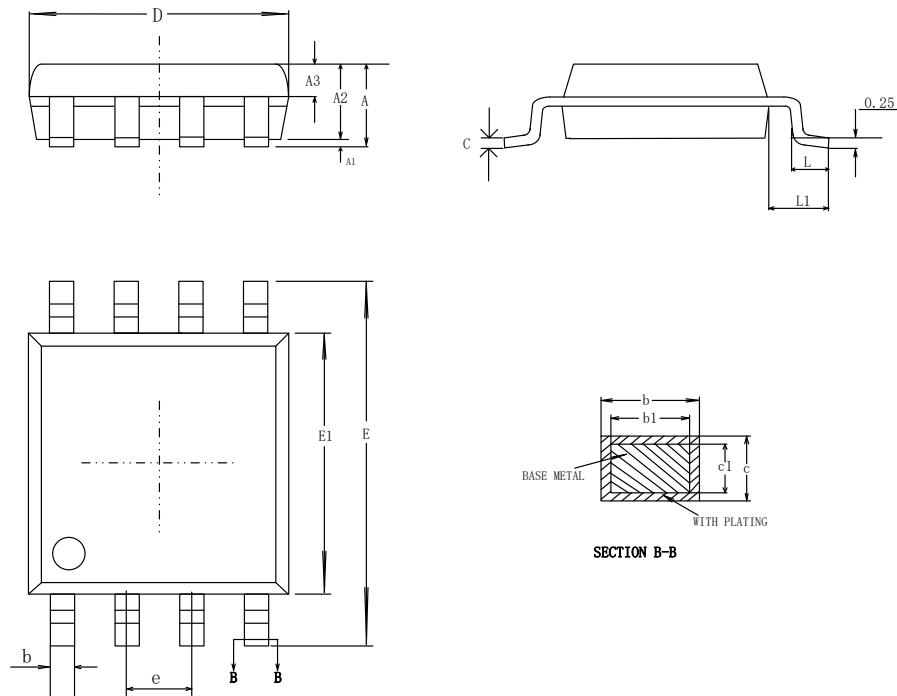
## Reference Schematic



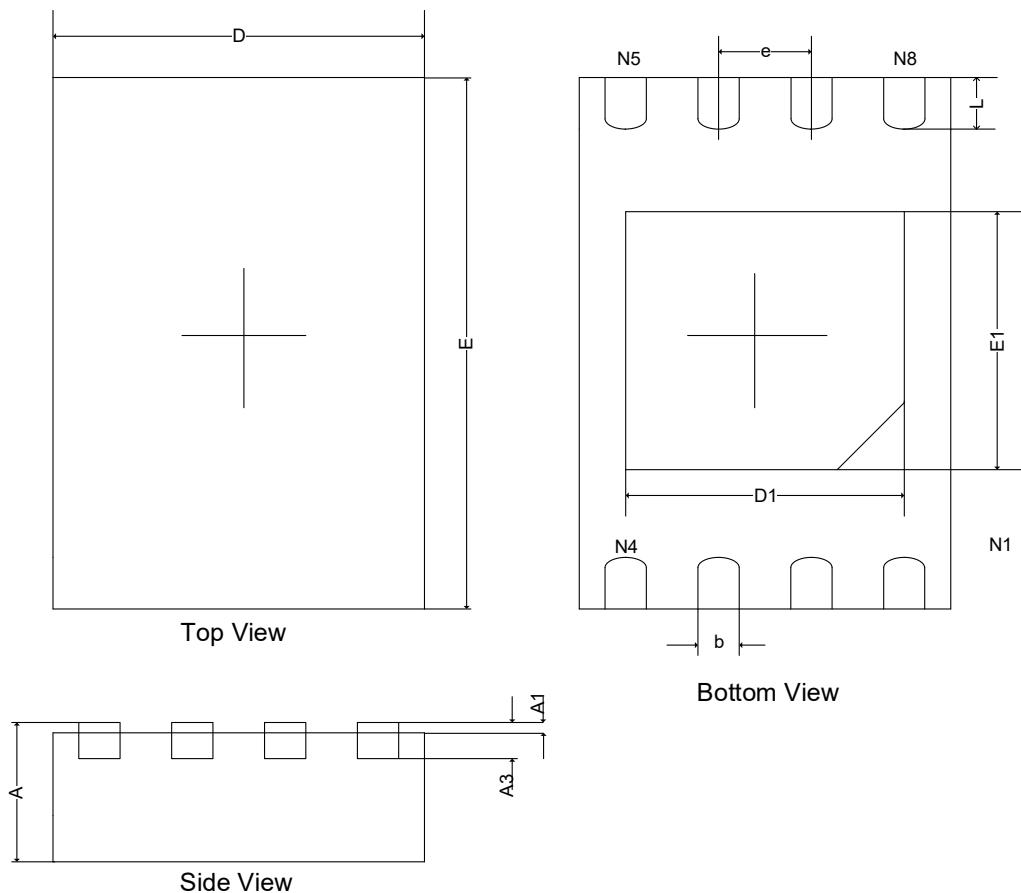
Reference Schematic for 10 cells

## Package Information

### MSOP8L PACKAGE OUTLINE DIMENSIONS



SYMBOL	MILLIMETER	
	MIN.	MAX.
A		1.10
A1	0.05	0.15
A2	0.75	0.95
A3	0.30	0.40
b	0.29	0.38
b1	0.28	0.33
c	0.15	0.20
c1	0.14	0.16
D	2.9	3.1
E	4.7	5.1
E1	2.9	3.1
e	0.65BSC	
L	0.40	0.70
L1	0.95BSC	

**DFN3X4-8L PACKAGE OUTLINE DIMENSIONS**

SYMBOL	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
A1	-	0.02	0.05
A3	0.18	0.20	0.25
D	2.90	3.00	3.10
E	3.90	4.00	4.10
D1	2.20	2.30	2.40
E1	1.70	1.80	1.90
b	0.15	0.20	0.25
e	0.65TYP.		
L	0.35	0.40	0.45

## Revision History

Release No.	Date	Revision Description
1.0	2015-12-24	Initial Release
1.1	2016-07-10	1. Corrects the format 2. Revised Open-wire Detection Delay
1.2	2016-11-10	1. Revised CW1051ALAM parameter 2. Add CW1051ALEM Ordering Information
1.3	2017-08-02	Add CW1051ALFM/ALFD Ordering Information
1.4	2017-10-17	Add CW1051ALGD Ordering Information
1.5	2017-11-17	1. Add CW1051ALHD/ALJM/ALKM Ordering Information 2. Revised VoCR parameter
1.6	2018-02-05	1. Add CW1051ALLM\ ALHM Ordering Information 2. Add Product Name 3. R6 parameter range modify to 200Ω~1000Ω. 4. CO PIN voltage range modify to -0.3V~VDD+0.3V.
1.7	2018-03-12	Add CW1051ALMM Ordering Information
1.8	2018-04-18	Add Reference Schematic
1.9	2018-06-19	Add CW1051ALOM\ ALPM\ ALQD \ALGM Ordering Information
2.0	2018-09-07	Add CW1051ALSM Ordering Information
2.1	2018-09-07	Add CW1051ALRM Ordering Information
2.2	2018-12-17	1. Add CW1051ALUM Ordering Information 2. Add ESD Ratings 3. Revised CO High Output Drive Ability parameter
2.3	2019-06-18	1. Add Reference Schematic 2. Add CW1051ALNM\ALVM\ALXM
2.4	2020-11-01	Add CW1051ALYM\ALTM\ALXD Ordering Information
2.5	2021-07-07	1. Adjusted Operation Temperature Range 2. Update Functional Block Diagram 3. Delay time sign is adjusted to lowercase "t" 4. Updated CO output drive ability and internal resistor 5. Add CW1051ALJD/ALRD 6. Add Reference Schematic 2 and 10 cell

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